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(74) Agents: KAWAMIYA, Osamu et al.; AOYAMA & PART-
NERS, IMP Building, 3-7, Shiromi 1-chome, Chuo-ku, Os-
aka-shi, Osaka, 5400001 (JP).

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(71) Applicant (for all designated States except US): MAT-
SUSHITA ELECTRIC WORKS, LTD. [JP/JP]; 1048,
Oaza-Kadoma, Kadoma-shi, Osaka, 5718686 (JP).

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(72) Inventors; and

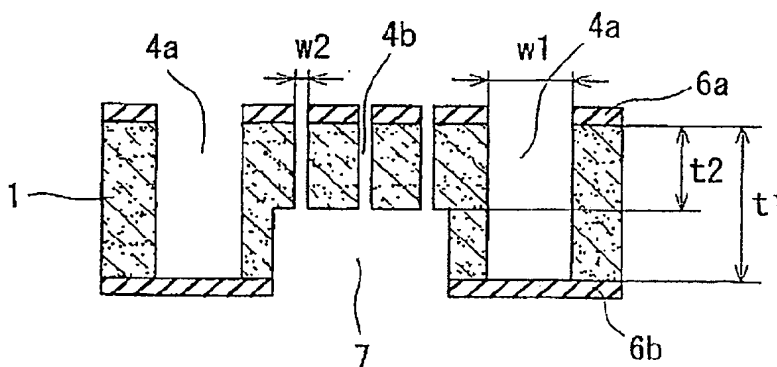
(75) Inventors/Applicants (for US only): GOUDA, Kazuo
[JP/JP]; c/o MATSUSHITA ELECTRIC WORKS, LTD.,
1048, Oaza-Kadoma, Kadoma-shi, Osaka, 5718686 (JP).
TSUJII, Koji [JP/JP]; c/o MATSUSHITA ELECTRIC
WORKS, LTD., 1048, Oaza-Kadoma, Kadoma-shi,
Osaka, 5718686 (JP). KIRIHARA, Masao [JP/JP];
c/o MATSUSHITA ELECTRIC WORKS, LTD., 1048,
Oaza-Kadoma, Kadoma-shi, Osaka, 5718686 (JP). NISHI-
JIMA, Youichi [JP/JP]; c/o MATSUSHITA ELECTRIC
WORKS, LTD., 1048, Oaza-Kadoma, Kadoma-shi, Osaka,
5718686 (JP).

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(54) Title: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE



(57) Abstract: Disclosed is
a method of manufacturing a
semiconductor device. In this
method, a concave portion (7)
is formed in one surface in the
thickness direction of a primary
base plate (1) comprising a
semiconductor substrate with a
relatively large thickness dimension.
Then, through-holes (4a, 4b) are
formed by a reactive-ion etching
process using as a mask an opening
(8) formed in an oxide film (6a)
provided on the other surface in the
thickness direction of the primary
base plate (1). The opening (8)
has a narrow width in a region

corresponding to the concave portion (7) and a wide width in the remaining region. Thus, respective times necessary for the
wide-width through-hole (4a) to penetrate through the primary base plate (1) and necessary for the narrow-width through-hole (4b)
to reach a bottom surface of the concave portion (7) can be approximately equalized to complete the common etching process of
the wide-width through-hole (4a) and the narrow-width through-hole (4b) approximately simultaneously.